

ABSTRACT OF THE DISCLOSURE

A process of selectively etching a sacrificial light absorbing material (SLAM) over a dielectric material, such as carbon doped oxide, on a substrate using a plasma of a gas mixture in a plasma etch chamber. The gas mixture comprises a hydrofluorocarbon gas, an optional hydrogen-containing gas, an optional fluorine-rich fluorocarbon gas, a nitrogen gas, an oxygen gas, and an inert gas. The process could provide a SLAM to a dielectric material etching selectivity ratio greater than 10:1.

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